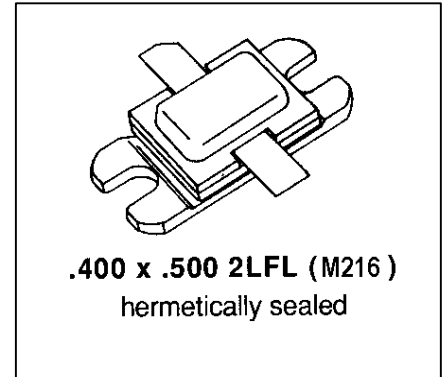


MS2231

RF AND MICROWAVE TRANSISTORS L-BAND APPLICATIONS

Features

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- LOW THERMAL RESISTANCE
- INPUT / OUTPUT MATCHING
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 100 \text{ W MIN.}$
- $G_P = 6.0 \text{ dB GAIN}$

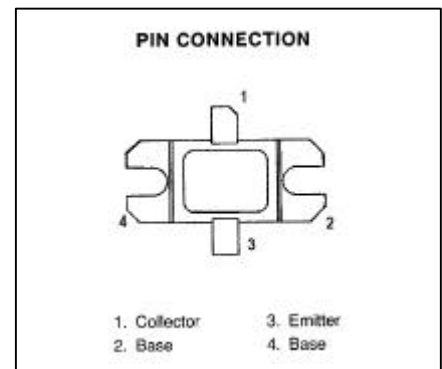


DESCRIPTION:

The MS2231 is a high-power Class C transistor specifically designed for L-Band Radar pulsed driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles, and temperatures and is capable of withstanding 3:1 output VSWR at rated RF conditions. Low RF thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The MS2231 is supplied in the grounded IMPAC™ hermetic metal/ceramic package with internal input/output matching structures.



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

| Symbol | Parameter | Value | Unit |
|------------|---|---------------|--------------------|
| P_{DISS} | Power Dissipation* ($T_C \leq 100^{\circ}\text{C}$) | 270 | W |
| I_C | Device Current* | 13.5 | A |
| V_{CC} | Collector-Supply Voltage* | 32 | V |
| T_J | Junction Temperature (Pulsed RF Operation) | 250 | $^{\circ}\text{C}$ |
| T_{STG} | Storage Temperature | - 65 to + 200 | $^{\circ}\text{C}$ |

Thermal Data

| | | | |
|---------------|-----------------------------------|------|----------------------|
| $R_{TH(j-c)}$ | Junction-Case Thermal Resistance* | 0.55 | $^{\circ}\text{C/W}$ |
|---------------|-----------------------------------|------|----------------------|

*Applies only to rated RF amplifier operation

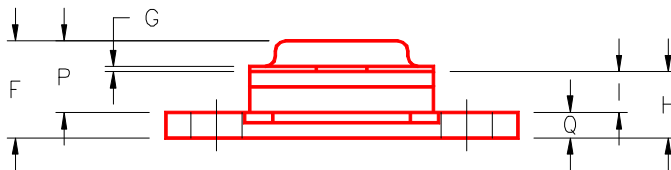
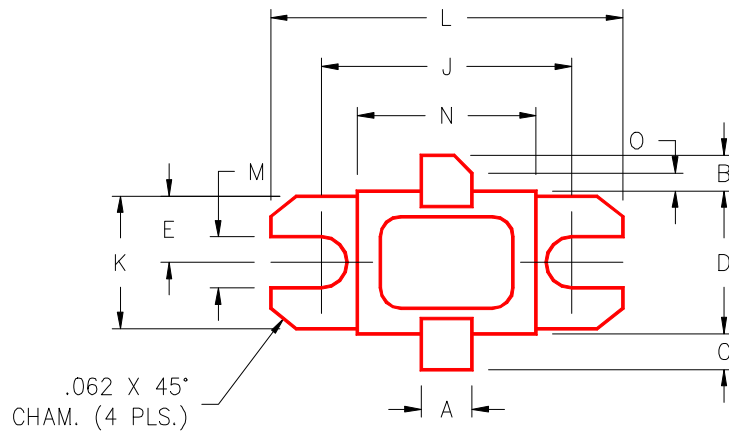
ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)
STATIC

| Symbol | Test Conditions | Value | | | Units |
|-------------------------|--|------------|------|-----------|-----------|
| | | Min. | Typ. | Max. | |
| BV_{CBO} | I_C = 50 mA I_E = 0 mA | 65 | | | V |
| BV_{EBO} | I_E = 10 mA I_C = 0 mA | 3.5 | | | V |
| BV_{CES} | I_C = 100 mA | 65 | | | V |
| I_{CES} | V_{BE} = 0 V V_{CE} = 32 V | | | 20 | mA |
| h_{FE} | V_{CE} = 5 V I_C = 5 A | 15 | | | |

DYNAMIC

| Symbol | Test Conditions | Value | | | Units |
|------------------------|--|------------|------|------|-----------|
| | | Min. | Typ. | Max. | |
| P_{OUT} | f = 1215 – 1400 MHz P_{IN} = 25 W V_{CE} = 28 V | 100 | | | W |
| ç_C | f = 1215 – 1400 MHz P_{IN} = 25 W V_{CE} = 28 V | 50 | | | % |
| G_P | f = 1215 – 1400 MHz P_{IN} = 25 W V_{CE} = 28 V | 6 | | | dB |

Note: Pulse width = 100µSec
 Duty Cycle = 10%

PACKAGE MECHANICAL DATA
PACKAGE STYLE M216


| | MINIMUM INCHES/MM | MAXIMUM INCHES/MM | | MINIMUM INCHES/MM | MAXIMUM INCHES/MM |
|---|----------------------|----------------------|---|----------------------|----------------------|
| A | .140/3,56 | | J | .700/17,78 | |
| B | .110/2,80 | | K | .386/9,80 | |
| C | .110/2,80 | | L | .900/22,86 | |
| D | .395/10,03 | .407/10,34 | M | .120/3,05 | |
| E | .193/4,90 | | N | .500/12,70 | |
| F | | .230/5,84 | O | .050/1,27 | |
| G | .003/0,08 | .006/0,15 | P | | .170/4,32 |
| H | .118/3,00 | .131/3,33 | Q | .062/1,58 | |
| I | .063/1,60 | | | | |